

	Type	L #	Hi ts	Search Text	DBs	Time Stamp	Error Corr mDr merr efor nirt ns si tio
1	IS &R	L1	2	("6656811").PN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 17:24	0
2	BR S	L2	1	"6261892".PN.	USPAT; US-PGPUB	2004/05/01 17:28	0
3	BR S	L3	1	"6424044".PN.	USPAT; US-PGPUB	2004/05/01 17:26	0
4	BR S	L5	0	"2002/0037648".PN.	USPAT; US-PGPUB	2004/05/01 17:27	0
5	BR S	L6	1	"6424044".PN.	USPAT; US-PGPUB	2004/05/01 17:28	0
6	BR S	L9	0	"2002/0081840".PN.	USPAT; US-PGPUB	2004/05/01 17:36	0
7	IS &R	L1 0	2	("20020030280").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 17:29	0
8	IS &R	L1 1	2	("20020037648").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 17:29	0
9	IS &R	L1 2	2	("20020081840").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 17:36	0
10	BR S	L1 3	59 01 9	bipolar near transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 17:37	0
11	BR S	L1 4	16 5	bipolar near transistor with carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 17:38	0
12	BR S	L1 5	78	bipolar near transistor with carbide and base with collector	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 17:39	0

Type	L #	Hits	Search Text	DBs	Time Stamp	E r r o r C o o r m D r m e r e f o n i r t n s i t i o
13	BR S	L1 6	bipolar near transistor with carbide and base with collector and (emitter adj base or "emitter-base" or base adj emitter or base-emitter)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 17:41,	0
14	BR S	L1 9	bipolar near transistor with carbide and base with collector and (emitter adj base or "emitter-base" or base adj emitter or base-emitter) with (open\$6 or expos\$6 or hole or etch\$6 or via) and oxide with carbide and emitter with (poly or polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 17:44	0

	Type	L #	Hi ts	Search Text	DBs	Time Stamp	E r r C o o r m D r m e r e f o n i r t n s s i t i o
15	BR S	L1 8	4	bipolar near transistor with carbide and base with collector and (emitter adj base or "emitter-base" or base adj emitter or base-emitter) and oxide with carbide and emitter with (poly or polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 17:45	0
16	BR S	L1 7	11	bipolar near transistor with carbide and base with collector and (emitter adj base or "emitter-base" or base adj emitter or base-emitter) and oxide with carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 17:49	0
17	BR S	L2 0	15	bipolar near transistor and emitter with carbide with base and base with collector and oxide with carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 17:57	0

	Type	L #	Hi ts	Search Text	DBs	Time Stamp	E r r C o o r m D r m e f o n i r t n s s i t i o
18	BR S	L2 1	87	bipolar near transistor and emitter with base and base with collector with oxide with carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 17:57	0
19	BR S	L2 2	44	bipolar near transistor and emitter with base and base with collector and oxide with carbide and emitter with open\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 18:21	0
20	BR S	L2 3	6	bipolar near transistor and emitter with (etch\$6 or open\$6 or hole) with oxide with carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 18:24	0
21	BR S	L2 4	7	bipolar near transistor and emitter same (etch\$6 or open\$6 or hole) with oxide with carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 18:42	0
22	BR S	L2 5	5	bipolar near transistor and (etch\$6 or open\$6 or hole) with oxide with carbide with base	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 18:44	0

	Type	L #	Hi ts	Search Text	DBs	Time Stamp	E r r o r C o r E m D r m e r n e f o r n i r t n s i t i o
23	BR S	L2 6	32	bipolar near transistor and (etch\$6 or open\$6 or hole) with oxide with carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 19:10	0
24	BR S	L2 7	40	(bipolar near transistor or hbt or bicmos) and (etch\$6 or open\$6 or hole) with oxide with carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 19:11	0
25	BR S	L2 8	13	(bipolar near transistor or hbt or bicmos) and (etch\$6 or open\$6 or hole) with oxide with carbide and emitter and base and collector	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 19:13	0
26	BR S	L2 9	0	20030096486.UR PN.	USPAT	2004/05/01 19:12	0
27	BR S	L3 0	23	(bipolar near transistor or hbt or bicmos) and (etch\$6 or open\$6 or hole) and oxide with carbide and emitter and base and collector	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 19:13	0

		Type	L#	Hits	Search Text	DBs	Time Stamp	E r r C o o r E m D r m e r n i r t n s s i t i o
28	BR S	L3 1	61		(bipolar near transistor or hbt or bicmos) and (etch\$6 or open\$6 or hole) with emitter and oxide with carbide and base and collector	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 19:13	0
29	BR S	L3 2	56		(bipolar near transistor or hbt or bicmos) and (etch\$6 or open\$6 or hole) with emitter and oxide with carbide and base with collector	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 19:29	0
30	BR S	L3 3	55		(bipolar near transistor or hemt) and (etch\$6 or open\$6 or hole) with emitter and oxide with carbide and base with collector	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 19:34	0
31	BR S	L3 4	3		("6255211" "6261892" "6424044" "2002/0030280" "2002/0037648" "2002/0081840") .PN.	USPAT	2004/05/01 19:30	0

		Type	L#	Hi ts	Search Text	DBs	Time Stamp	E r r C o o r E m D r m e f o n i r t n s s i t i o
32	BR S	L3 5	2		hemt and (etch\$6 or open\$6 or hole) with emitter and oxide with carbide and base with collector	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 19:32	0
33	BR S	L3 6	0		hjbt and (etch\$6 or open\$6 or hole) with emitter and oxide with carbide and base with collector	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 19:32	0
34	BR S	L3 7	31		hbt and (etch\$6 or open\$6 or hole) with emitter and oxide with carbide and base with collector	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 19:34	0
35	BR S	L3 8	49		bipolar near transistor and (etch\$6 or open\$6 or hole) with emitter and base with carbide and collector	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 21:10	0
36	BR S	L3 9	8		5378921.URPN.	USPAT	2004/05/01 20:52	0

	Type	L #	Hits	Search Text	DBs	Time Stamp	E r r o r C o o r E m D r m e r e f o n i r t n s s i t i o
37	BR S	L4 0	0	bipolar near transistor and base with carbide and (etch\$6 or open\$6 or hole) with base with carbide and collector and emitter with (etch\$6 with open\$6 with hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 21:12	0
38	BR S	L4 1	12	bipolar near transistor and base with carbide and (etch\$6 or open\$6 or hole) with base with carbide and collector and emitter with (etch\$6 or open\$6 or hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/01 21:13	0